Trend of Functional Atomic Thin Film Research-Thin Film Growth-

Atsushi Ando (AIST), Hirokazu Fukidome (Tohoku Univ.)

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Concluding remarks -Current status and prospects: Growth techniques for atomic layers of transition metal dichalcogenides-

〇Shintaro Sato¹ (1.Fujitsu Labs)

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Transition metal dichalcogenides can have a band gap depending on the composition, in contrast to graphene, and are expected to be used for transistors and optical devices in the future. For realizing such application, however, it is required to grow TMDCs uniformly over a large area, which has not yet been realized. In this symposium, state-of-art growth techniques have been described by the leading researchers in Japan. As concluding remarks, I briefly review growth technologies for TMDC worldwide and discuss issues to address and future directions.